

Description

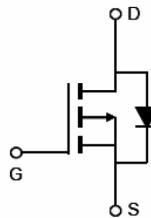
The VS15P03-S8 uses advanced trench technology to provide excellent $R_{DS(ON)}$. This device is suitable for use as a load switch or in PWM applications.

General Features

- $V_{DS} = -30V, I_D = -15A$
- $R_{DS(ON)} < 12m\Omega @ V_{GS}=-10V$
- $R_{DS(ON)} < 15m\Omega @ V_{GS}=-4.5V$
- High power and current handling capability
- Lead free product is acquired
- Surface mount package

Application

- PWM applications
- Load switch
- Uninterruptible power supply



Schematic diagram



Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
VS15P03-S8	VS15P03-S8	SOP-8	Ø330mm	12mm	

Absolute Maximum Ratings ($T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	-15	A
Drain Current-Pulsed ^(Note 1)	I_{DM}	-80	A
Maximum Power Dissipation	P_D	3.1	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	$^\circ C$

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient ^(Note 2)	$R_{\theta JA}$	40	$^\circ C/W$
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Electrical Characteristics ($T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V I_D=-250\mu A$	-30	-33	-	V

Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-30V, V _{GS} =0V	-	-	-1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
On Characteristics <small>(Note 3)</small>						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =-250μA	-0.8	-1.25	-2.2	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =-10V, I _D =-15A	-	8.5	12	mΩ
		V _{GS} =-4.5V, I _D =-10A	-	11.5	15	mΩ
Forward Transconductance	g _{FS}	V _{DS} =-5V, I _D =-15A	30	-	-	S
Dynamic Characteristics <small>(Note 4)</small>						
Input Capacitance	C _{iss}	V _{DS} =-15V, V _{GS} =0V, F=1.0MHz	-	2900	-	PF
Output Capacitance	C _{oss}		-	410	-	PF
Reverse Transfer Capacitance	C _{rss}		-	280	-	PF
Switching Characteristics <small>(Note 4)</small>						
Turn-on Delay Time	t _{d(on)}	V _{DD} =-15V, ID=-10A, V _{GS} =-10V, R _{GEN} =3Ω	-	15	-	nS
Turn-on Rise Time	t _r		-	11	-	nS
Turn-Off Delay Time	t _{d(off)}		-	44	-	nS
Turn-Off Fall Time	t _f		-	21	-	nS
Total Gate Charge	Q _g	V _{DS} =-15V, I _D =-10A, V _{GS} =-10V	-	48	-	nC
Gate-Source Charge	Q _{gs}		-	12	-	nC
Gate-Drain Charge	Q _{gd}		-	14	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage <small>(Note 3)</small>	V _{SD}	V _{GS} =0V, I _S =-2A	-	-	-1.2	V

Notes

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production

Typical Electrical and Thermal Characteristics

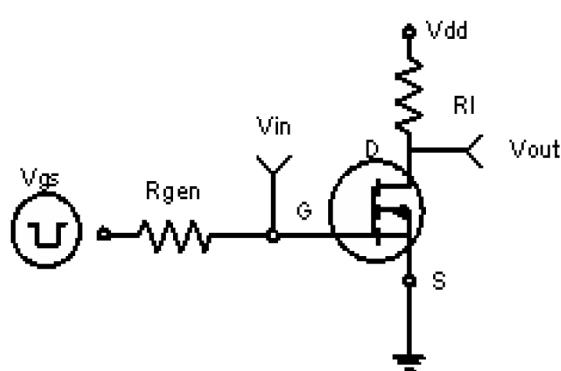


Figure 1 Switching Test Circuit

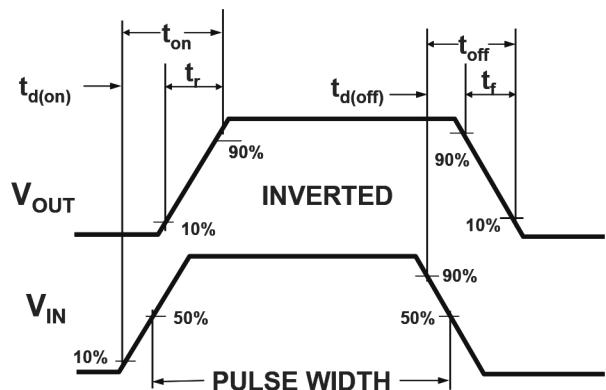


Figure 2 Switching Waveforms

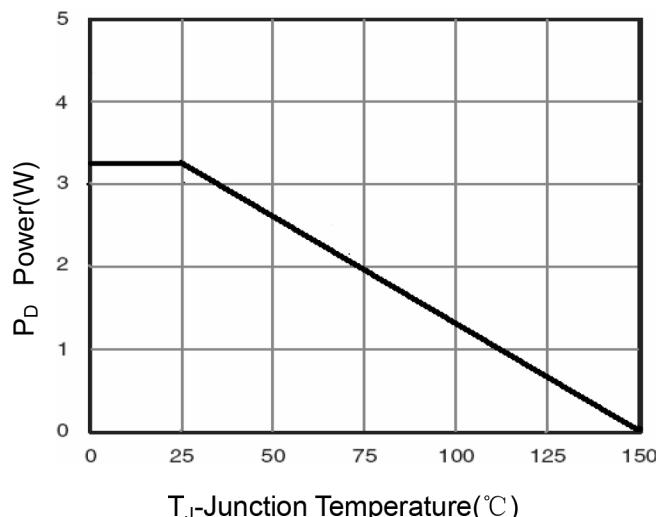


Figure 3 Power Dissipation

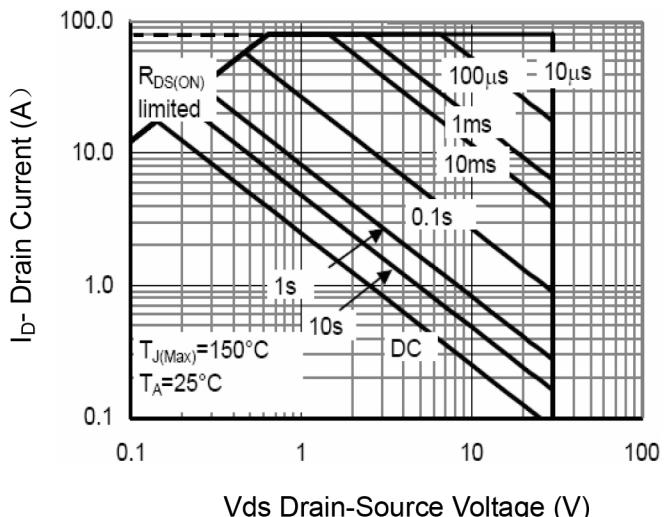


Figure 4 Safe Operation Area

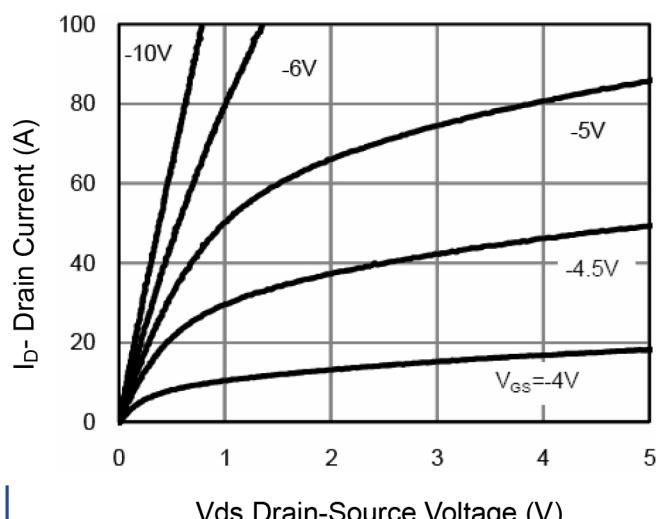


Figure 5 Output Characteristics

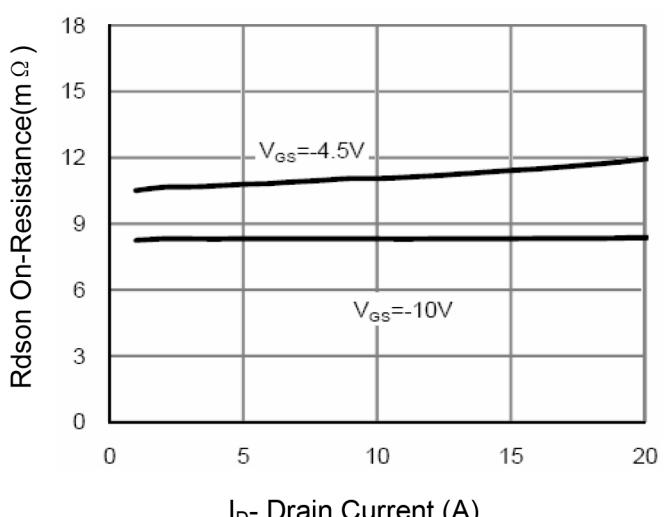
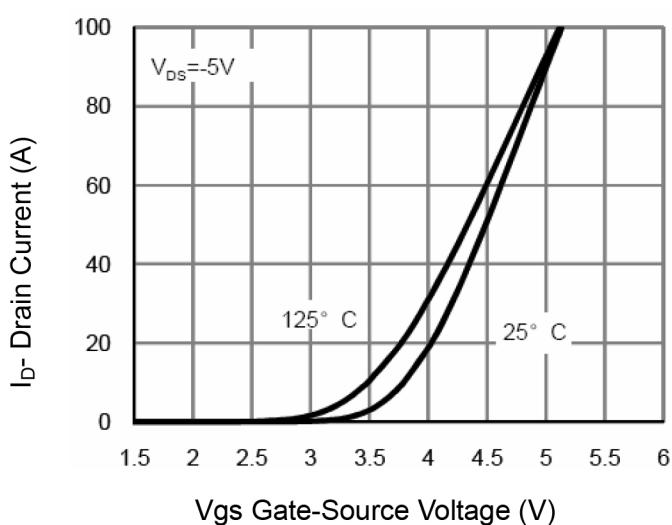
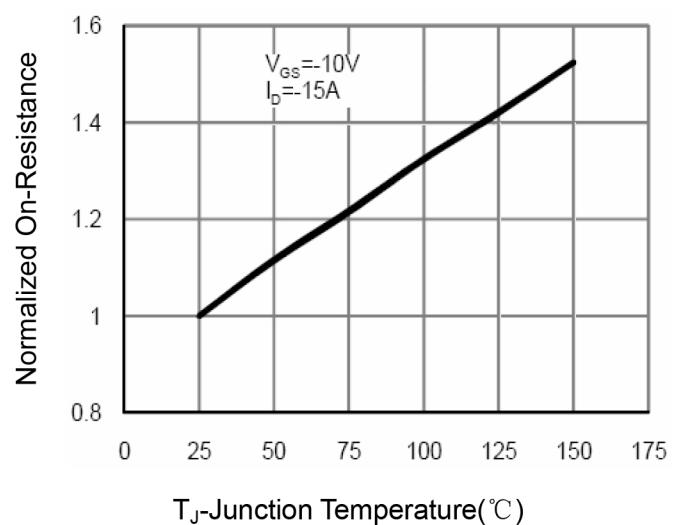
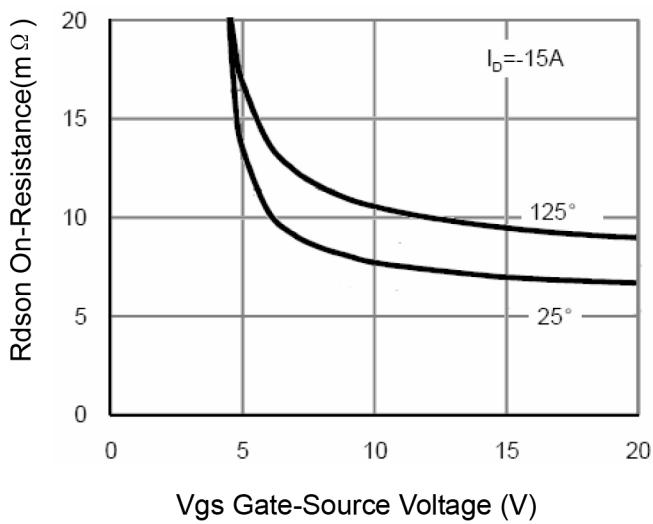
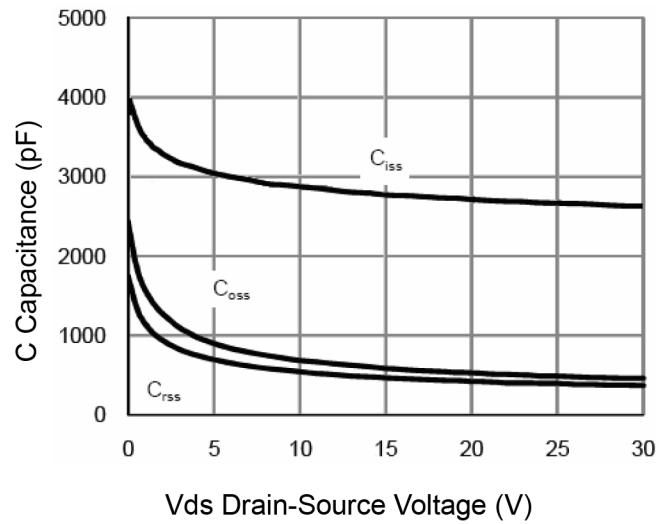
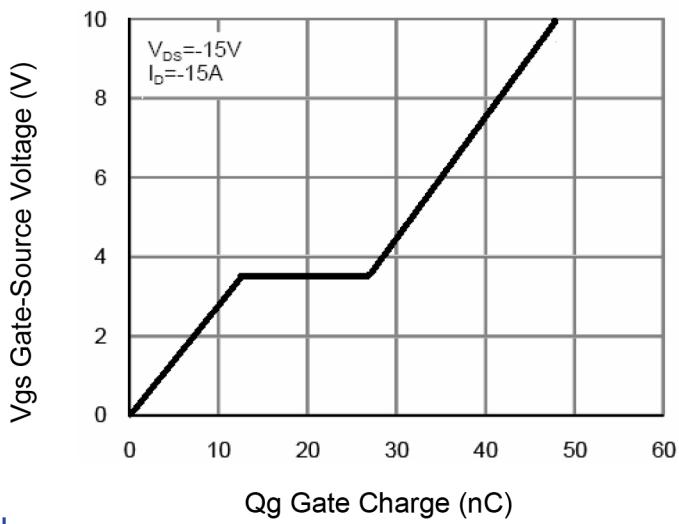
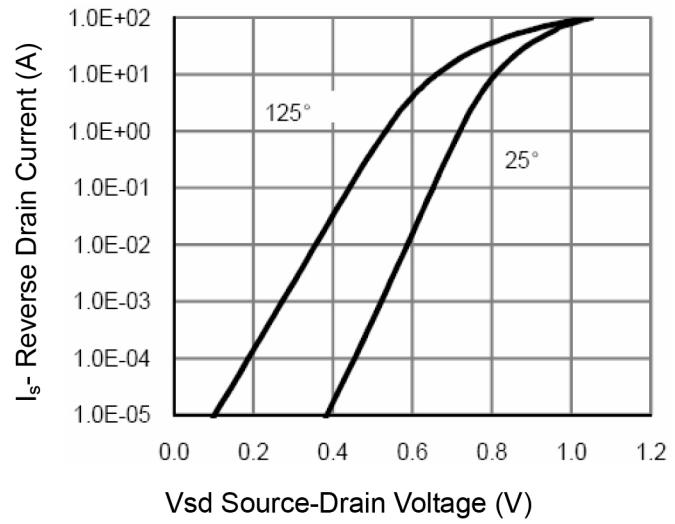


Figure 6 Drain-Source On-Resistance


Figure 7 Transfer Characteristics

Figure 8 Drain-Source On-Resistance

Figure 9 R_{DSON} vs V_{GS}

Figure 10 Capacitance vs V_{DS}

Figure 11 Gate Charge

Figure 12 Source- Drain Diode Forward

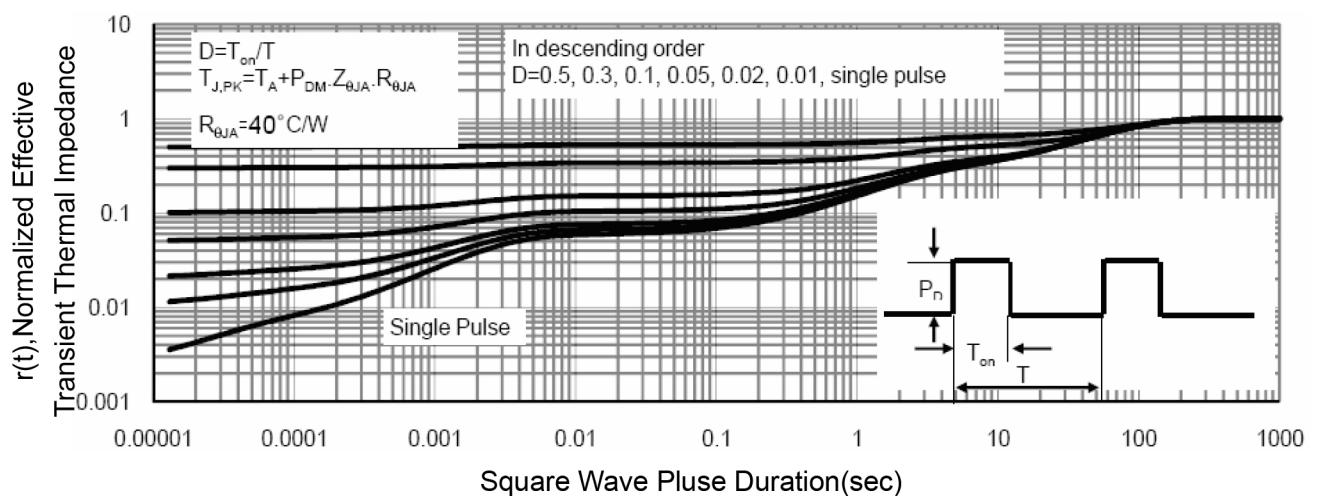


Figure 13 Normalized Maximum Transient Thermal Impedance